

In the Claims:

1-14. canceled.

15 (currently amended) A silicon single crystal wafer for a particle monitor, said wafer comprising a low particle density wafer body having a low density of COP's along an entire thickness of the wafer body, the entire thickness including a surface portion of the wafer body, wherein the surface portion has a surface density of crystal-originated particles of not more than 15 counts/cm², the crystal-originated particles counted as part of the surface density having a particle size of not less than 0.12 μ m, the surface density of crystal-originated particles present even after repeating a Standard Cleaning -1, which is made using alkaline chemical liquid mainly containing NH₄OH, H₂O₂, and H₂O,

the wafer body and surface portion derived from an ingot that has been grown using the Czochralski method and then sliced to form the wafer body, growing of the ingot including a step of controlling a time period of passing the ingot through a temperature range from 1150°C to 1070°C to be within 20 minutes and controlling a time period of passing the ingot through a temperature range from 900°C to 800°C to be within 40 minutes so as to form a low density of COPs in the ingot along a direction of pulling the ingot, said step minimizing a size of the crystal-originated particles and the presence of bulk micro-defects so as to form the low particle density wafer body with the low density of COPs along the entire thickness of the wafer body and in the surface portion, the formed low particle density wafer body and surface portion having a crystal-originated particle density such that removal of a part of the surface portion as a result of repeated Standard Cleaning -1 steps produces a remaining surface portion that still has the surface density of crystal-originated particles of not more than 15 counts/cm².

16. (previously presented) The wafer of claim 15, wherein said wafer has an oxygen concentration of not more than 13×10^{17} atoms/cm³ (old ASTM).

17. (previously presented) The wafer of claim 15, wherein said silicon single crystal ingot has a nitrogen concentration of $1 \times 10^{13} - 1 \times 10^{15}$ atoms/cm³.

18. (previously presented) The wafer of claim 16, wherein said silicon single crystal ingot has a nitrogen concentration of $1 \times 10^{13} - 1 \times 10^{15}$ atoms/cm³.

19. (previously presented) The wafer of claim 15, wherein said low particle density wafer and surface portion with said crystal-originated particle density is such that removal of the part of the surface portion to produce the remaining surface portion still has the surface density of crystal-originated particles of not more than 15 counts/cm² when the Standard Cleaning -1 is repeated six times, and each cleaning is carried out for 10 minutes.